DATA SHEET

AS213-92, AS213-92LF: PHEMT GaAs IC SPDT Switch 0.1–3 GHz

Applications

- T/R switch in WLANs, Bluetooth and medium-power telecommunication applications

Features

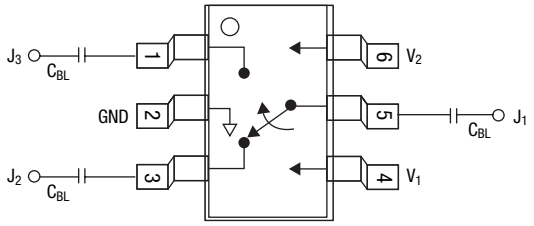
- Low insertion loss (0.4 dB @ 2.4 GHz)
- Isolation 22 dB @ 2.4 GHz
- Low DC power consumption
- PHEMT process
- Operates with 1.8 V control voltage
- Available lead (Pb)-free and RoHS-compliant MSL-1 @ 260 °C per JEDEC J-STD-020

Description

The AS213-92 is a medium-power IC FET SPDT switch in a low-cost miniature SC-70 6-lead plastic package. The AS213-92 features low insertion loss and positive voltage operation with very low DC power consumption. This general-purpose switch can be used in a variety of telecommunications applications.

NEW Skyworks offers lead (Pb)-free, RoHS (Restriction of Hazardous Substances)-compliant packaging.

Pin Out



DC blocking capacitors (C_{BL}) must be supplied externally for positive voltage operation. C_{BL} = 100 pF for operation >500 MHz.

Electrical Specifications at 25 °C (0, 3 V)

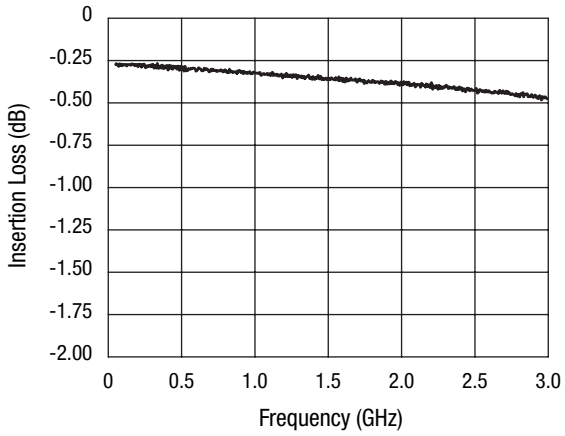
Parameter[1]	Frequency	Min.	Typ.	Max.	Unit
Insertion loss[2]	0.1–1.0 GHz		0.3	0.5	dB
	1.0–2.0 GHz		0.4	0.6	dB
	2.0–3.0 GHz		0.5	0.7	dB
Isolation	0.1–1.0 GHz	24	27		dB
	1.0–2.0 GHz	20	23		dB
	2.0–3.0 GHz	16	19		dB
VSWR[3]	0.1–1.0 GHz		1.3:1		
	1.0–3.0 GHz		1.4:1		

1. All measurements made in a 50 Ω system, unless otherwise specified.
2. Insertion loss changes by 0.003 dB/°C.
3. Insertion loss state.

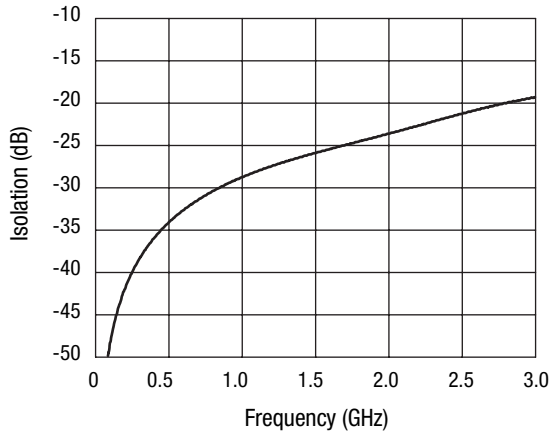
Operating Characteristics at 25 °C (0, 3 V)

Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching characteristics						
Rise, fall	10/90% or 90/10% RF			10		ns
On, off	50% CTL to 90/10% RF			20		ns
Video feedthru	T_{RISE} = 1 ns, BW = 500 MHz			25		mV
Input power for 1 dB compression	0/1.8 V	0.5–3 GHz		20		dBm
	0/3 V	0.5–3 GHz		27		dBm
Intermodulation intercept point (IP3)	For two-tone input power 5 dBm					
	0/3 V	0.5–3 GHz		40		dBm
Thermal resistance				25		°C/W
Control voltages	V_{LOW} = 0 to 0.2 V @ 20 µA max. V_{HIGH} = 1.8 V @ 100 µA max. to 5 V @ 200 µA max.					

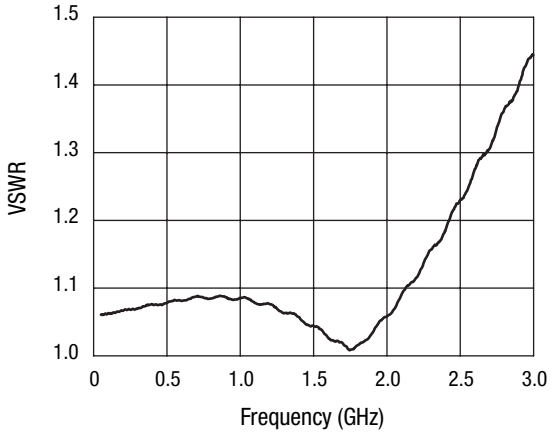
Simulated Performance Data (0, 3 V)



Insertion Loss vs. Frequency



Isolation vs. Frequency



VSWR vs. Frequency

Absolute Maximum Ratings

Characteristic	Value
RF input power	2 W max. for f > 500 MHz 500 mW for f < 500 MHz V_{CTL} = 0/8 V
Supply voltage	8 V
Control voltage	-0.2 V, +8 V
Operating temperature	-40 °C to +85 °C
Storage temperature	-65 °C to +150 °C

Performance is guaranteed only under the conditions listed in the specifications table and is not guaranteed under the full range(s) described by the Absolute Maximum specifications. Exceeding any of the absolute maximum/minimum specifications may result in permanent damage to the device and will void the warranty.

CAUTION: *Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions must be employed at all times.*

Recommended Solder Reflow Profiles

Refer to the *"Recommended Solder Reflow Profile"* Application Note.

Tape and Reel Information

Refer to the *"Discrete Devices and IC Switch/Attenuators Tape and Reel Package Orientation"* Application Note.

Truth Table

V_1	V_2	J_1–J_2	J_1–J_3
0	V_{HIGH}	Isolation	Insertion loss
V_{HIGH}	0	Insertion loss	Isolation

Any state other than described in the truth table will put the device in an undefined state. An undefined state will not damage the device.
V_{HIGH} = 1.8 to 5 V.

SC-70 6 Lead